

N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 24 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

Quick reference data

Table 1.

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

	Quient reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	-	-	37	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	29	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 12</u>	-	12.3	14.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	9.9	11.6	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I _D = 10 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	1.4	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I _D = 10 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	4.9	-	nC

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Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		5
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S

SOT669 (LFPAK; Power-SO8)

Ordering information 3.

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN011-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

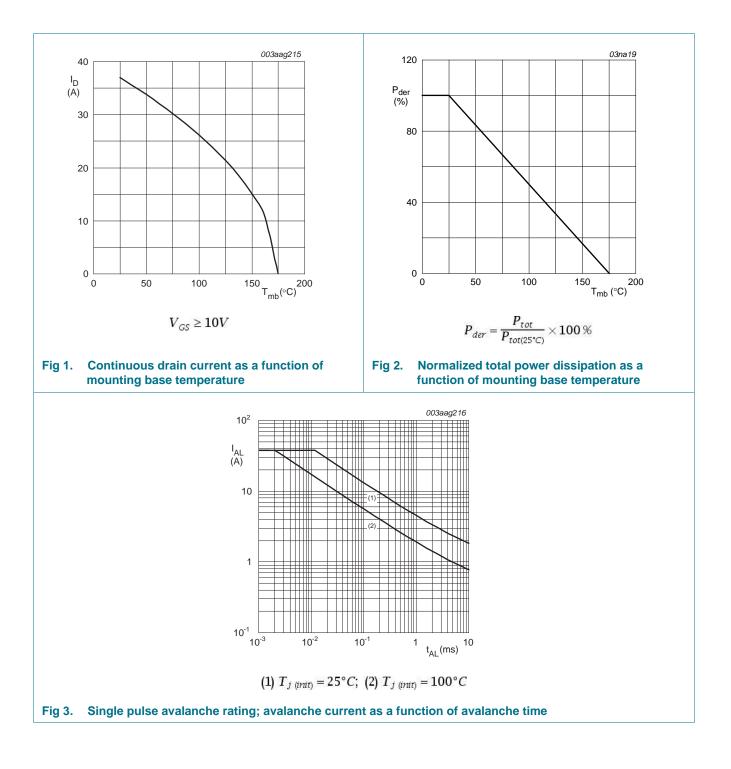
Limiting values 4.

Table 4. **Limiting values**

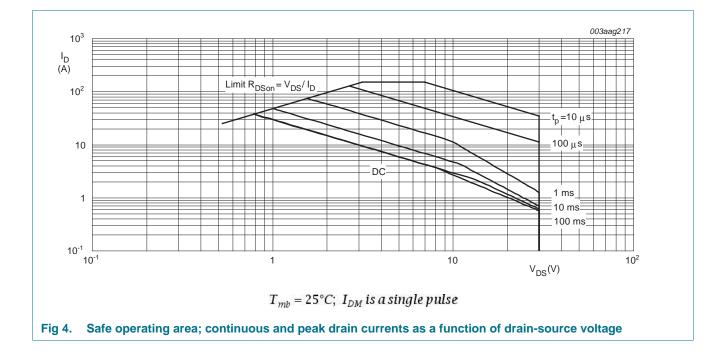
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	37	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	26	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	150	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	29	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	140	-	V
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	26	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	150	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 37 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω ; unclamped; see Figure 3	-	9	mJ

PSMN011-30YLC



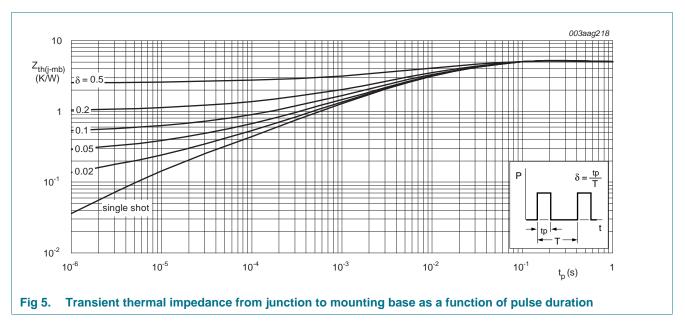
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	4.87	5.06	K/W



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6. Characteristics

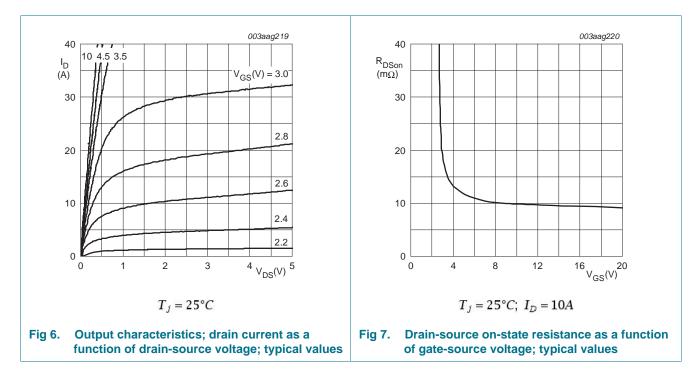
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.57	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 12</u>	-	12.3	14.5	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	23.4	mΩ
	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 12</u>	-	9.9	11.6	mΩ	
	V _{GS} = 10 V; I _D = 10 A; T _j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	18.8	mΩ	
R _G	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
Q _{G(tot)} total gate	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	10.3	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	9	-	nC
Q _{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	1.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	1.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.4	-	nC
Q _{GD}	gate-drain charge		-	1.4	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.5	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	641	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	146	-	pF
C _{rss}	reverse transfer capacitance		-	46	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_{L} = 0.6 Ω ; V_{GS} = 4.5 V;	-	13.4	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	12.7	-	ns
t _{d(off)}	turn-off delay time		-	16.8	-	ns
t _f	fall time			6.6		ns

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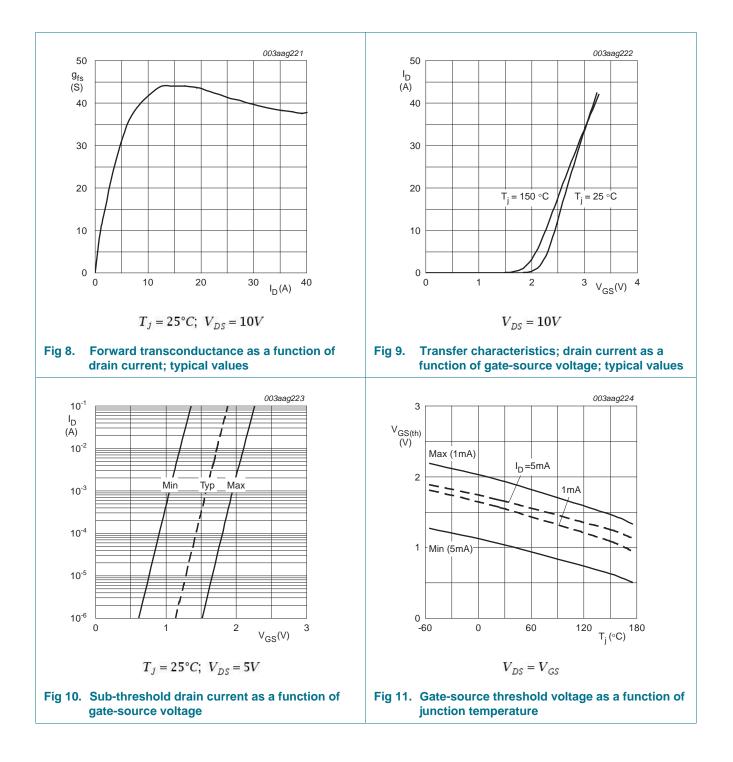
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	3.8	-	nC
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.85	1.1	V
t _{rr}	reverse recovery time	I _S = 10 A; dI _S /dt = -100 A/μs;	-	17	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	7	-	nC
t _a	reverse recovery rise time	V _{GS} = 0 V; I _S = 10 A;	-	10	-	ns
t _b	reverse recovery fall time	dI _S /dt = -100 A/µs; V _{DS} = 15 V; see <u>Figure 18</u>	-	7	-	ns



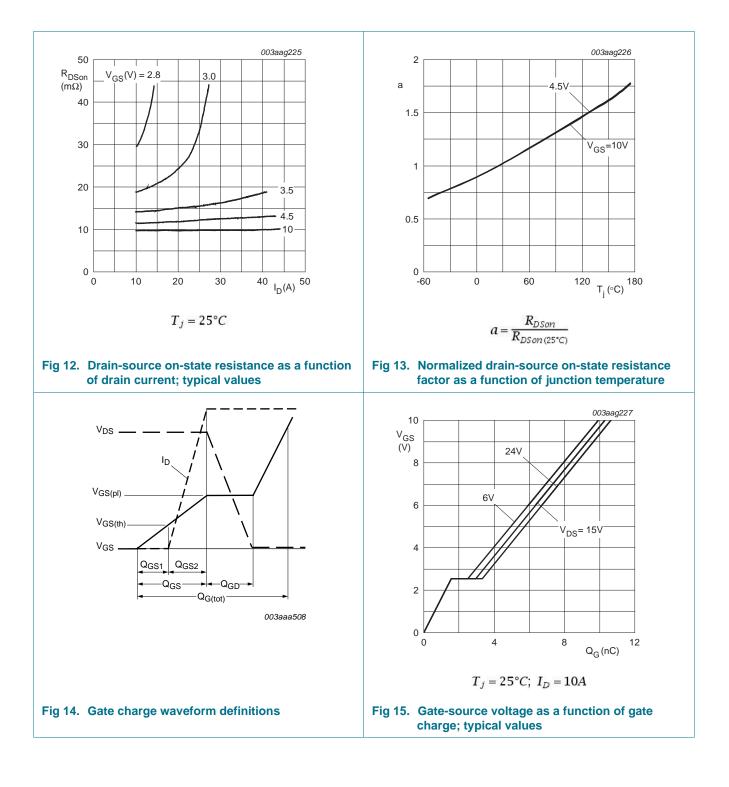
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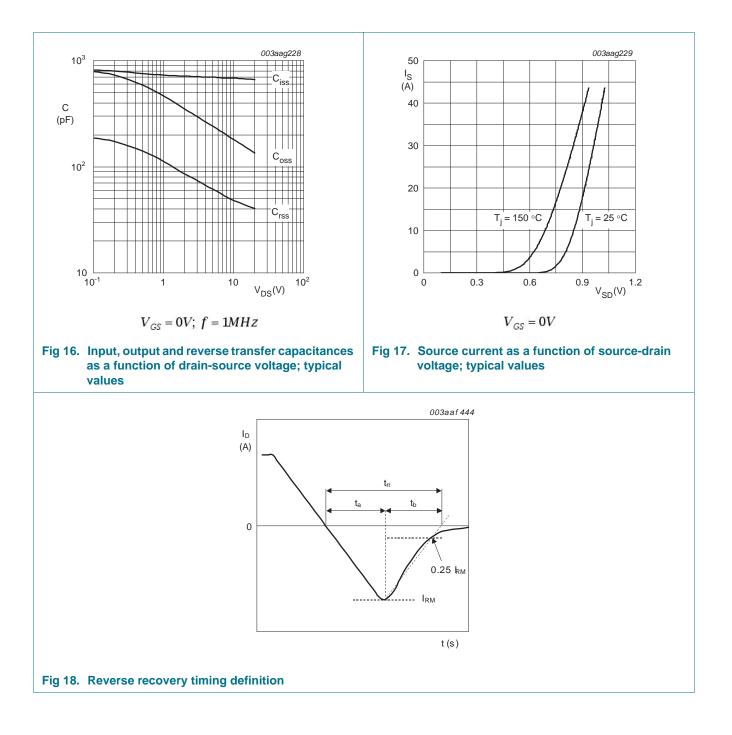


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7. Package outline

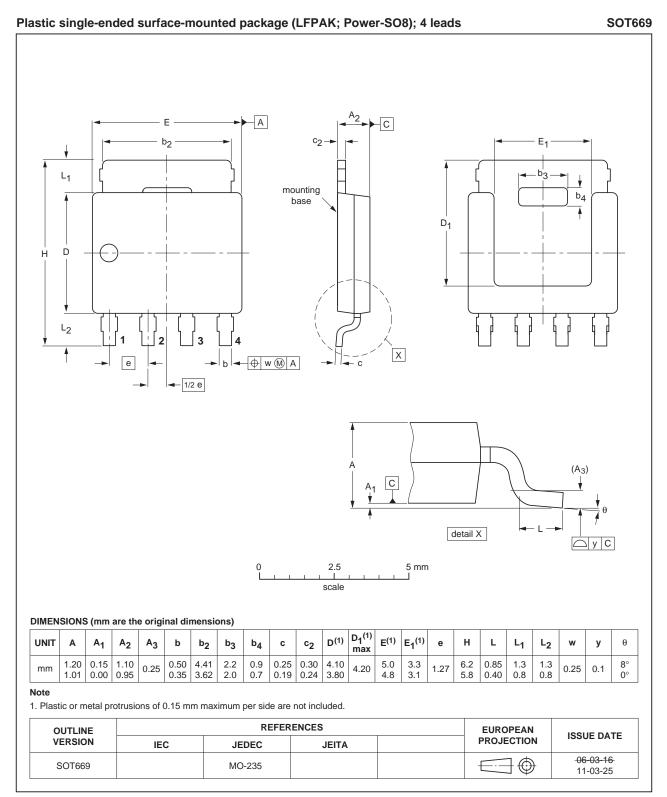


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN011-30YLC v.3	20111024	Product data sheet	-	PSMN011-30YLC v.2
Modifications:	 Data sheet sta 	tus changed from prelimina	ry to product.	
	 Various chang 	es to content.		
PSMN011-30YLC v.2	20110930	Preliminary data shee	t -	PSMN011-30YLC v.1

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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